

Sadao Haga, *et al.*  
U.S.S.N. 09/916,381  
Page 2 of 9

### AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

1. (Presently amended) An etching solution containing at least hydrofluoric acid, nitric acid and hexafluorosilicic acid, the concentration of the hexafluorosilicic acid being ~~not less than 10%~~ to 40% by weight based on the weight of the etching solution.
2. (Original) An etching solution according to claim 1, wherein the concentration of the hexafluorosilicic acid is 15 to 40% by weight based on the weight of the etching solution.
- 3 (Original) An etching solution according to claim 1, wherein the concentration of the hydrofluoric acid is 1 to 20% by weight based on the weight of the etching solution.
4. (Original) An etching solution according to claim 1, wherein the concentration of the nitric acid is 20 to 60% by weight based on the weight of the etching solution.
5. (Original) An etching solution according to claim 1, further comprising acetic acid.

BOS2\_466483\_1

Sadao Haga, *et al.*  
U.S.S.N. 09/916,381  
Page 3 of 9

6. (Original) An etching solution according to claim 5, wherein the concentration of the acetic acid is 0.01 to 5% by weight based on the weight of the etching solution.

7. (Original) An etching solution according to claim 1, which is used for etching a silicon substrate.

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (Canceled)

12. (Canceled)

13. (Canceled)

BOS2\_406683\_1